

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics¹⁾

Thermal resistance, junction - case	R_{thJC}		-	-	2	K/W
Thermal resistance, junction - ambient, leaded	R_{thJA}		-	-	100	
SMD version, device on PCB	R_{thJA}	minimal footprint	-	-	75	
		6 cm ² cooling area ²⁾	-	-	50	

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified

Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}, I_D=1\text{ mA}$	75	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=31\text{ }\mu\text{A}$	1.2	1.6	2.0	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=75\text{ V}, V_{GS}=0\text{ V}, T_j=25\text{ °C}$	-	0.01	1	μA
		$V_{DS}=75\text{ V}, V_{GS}=0\text{ V}, T_j=125\text{ °C}^{2)}$	-	1	100	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}, V_{DS}=0\text{ V}$	-	1	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=5\text{ V}, I_D=50\text{ A}$	-	58.0	65	m Ω
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}, I_D=50\text{ A},$	-	38.5	50.0	

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Dynamic characteristics¹⁾

Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=25\text{ V},$ $f=1\text{ MHz}$	-	630	-	pF
Output capacitance	C_{oss}		-	160	-	
Reverse transfer capacitance	C_{rss}		-	75	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=37\text{ V}, V_{GS}=10\text{ V},$ $I_D=22\text{ A}, R_G=9.1\ \Omega$	-	6	-	ns
Rise time	t_r		-	20	-	
Turn-off delay time	$t_{d(off)}$		-	26	-	
Fall time	t_f		-	10	-	

Gate Charge Characteristics¹⁾

Gate to source charge	Q_{gs}	$V_{DD}=60\text{ V}, I_D=22\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	2	2.7	nC
Gate to drain charge	Q_{gd}		-	9	12	
Gate charge total	Q_g		-	21	33	
Gate plateau voltage	$V_{plateau}$		-	3.9	-	V

Reverse Diode

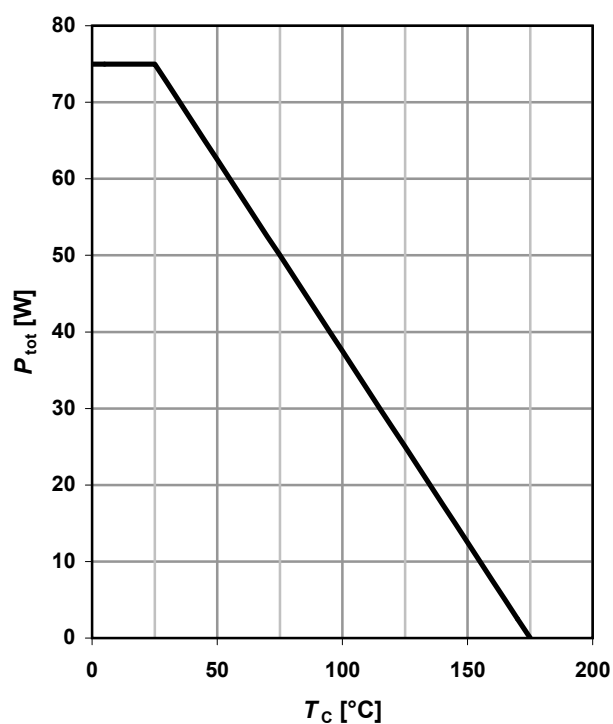
Diode continuous forward current ¹⁾	I_S	$T_C=25\text{ °C}$	-	-	25	A
Diode pulse current ¹⁾	$I_{S,pulse}$		-	-	100	
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=22\text{ A},$ $T_J=25\text{ °C}$	-	0.9	1.3	V
Reverse recovery time ¹⁾	t_{rr}	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	44	-	ns
Reverse recovery charge ¹⁾	Q_{rr}	$V_R=40\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	66	-	nC

¹⁾ Defined by design. Not subject to production test.

²⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

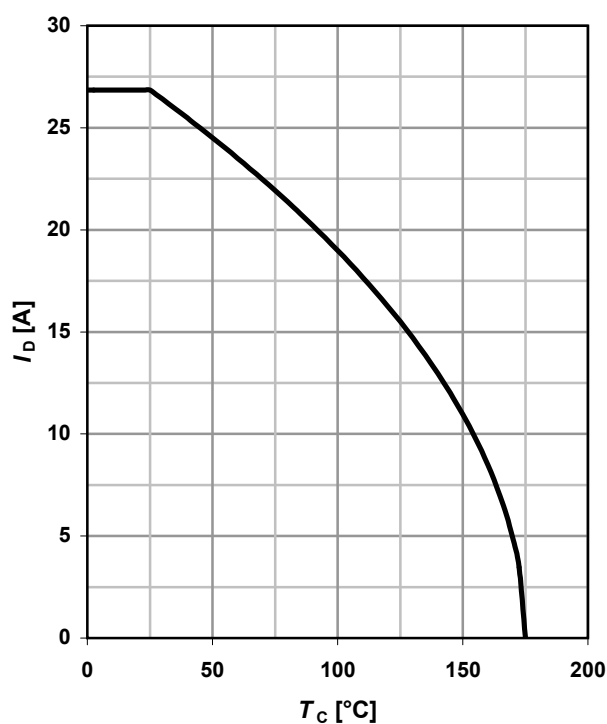
1 Power dissipation

$$P_{\text{tot}} = f(T_C); V_{\text{GS}} \geq 6 \text{ V}$$



2 Drain current

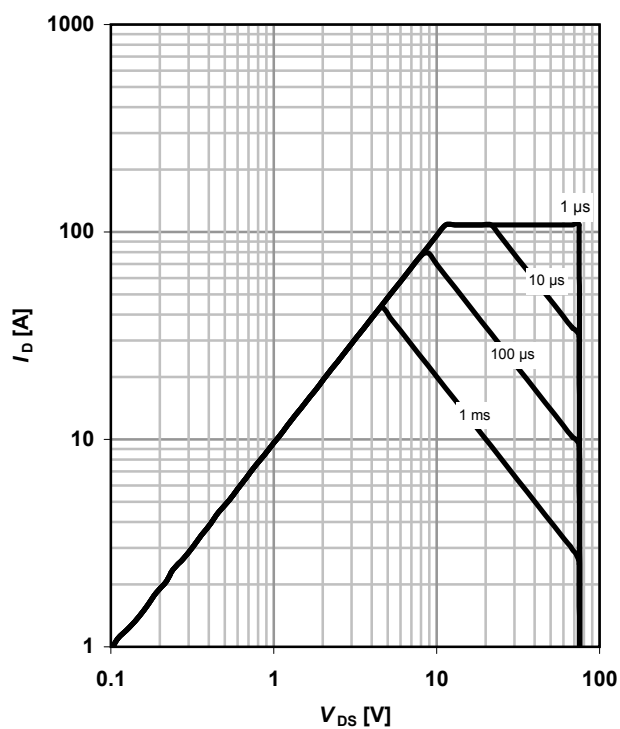
$$I_D = f(T_C); V_{\text{GS}} \geq 10 \text{ V}$$



3 Safe operating area

$$I_D = f(V_{\text{DS}}); T_C = 25^\circ\text{C}; D = 0$$

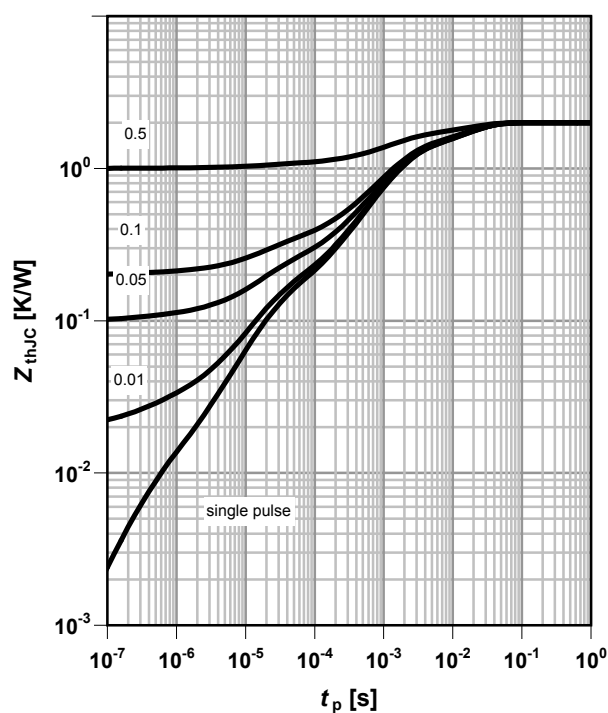
parameter: t_p



4 Max. transient thermal impedance

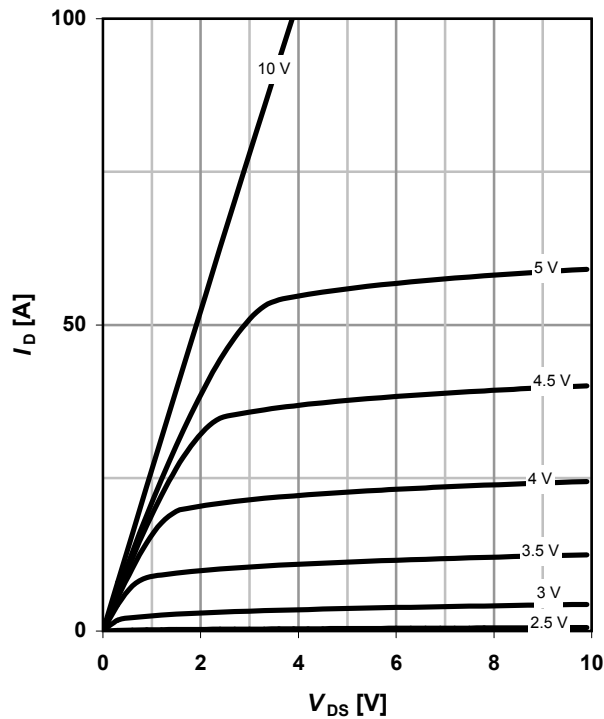
$$Z_{\text{thJC}} = f(t_p)$$

parameter: $D = t_p/T$



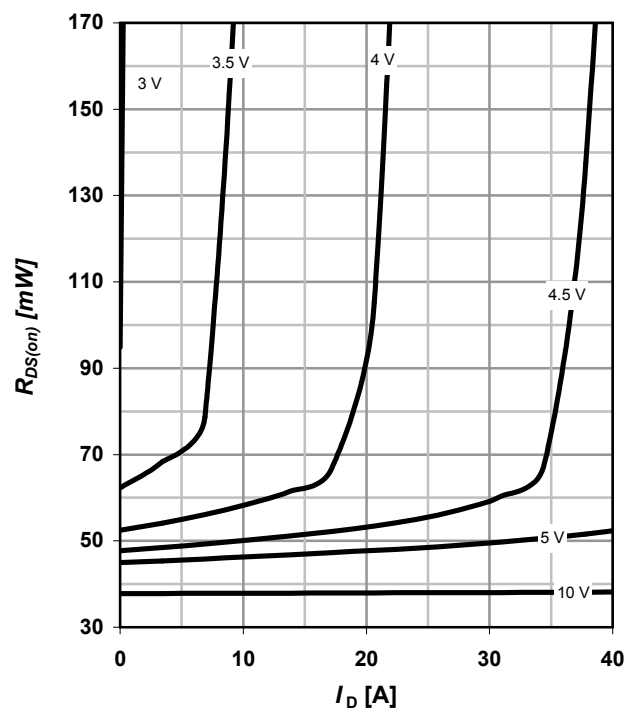
5 Typ. output characteristics

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}$

parameter: V_{GS}


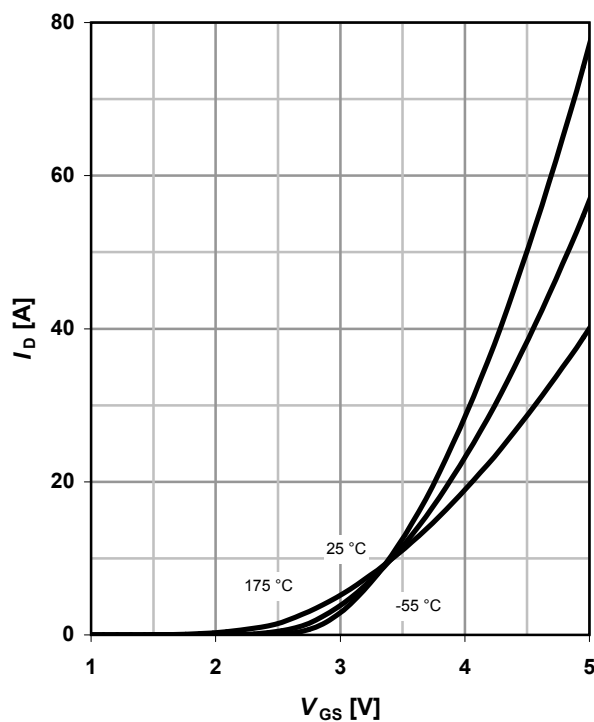
6 Typ. drain-source on-state resistance

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$

parameter: V_{GS}


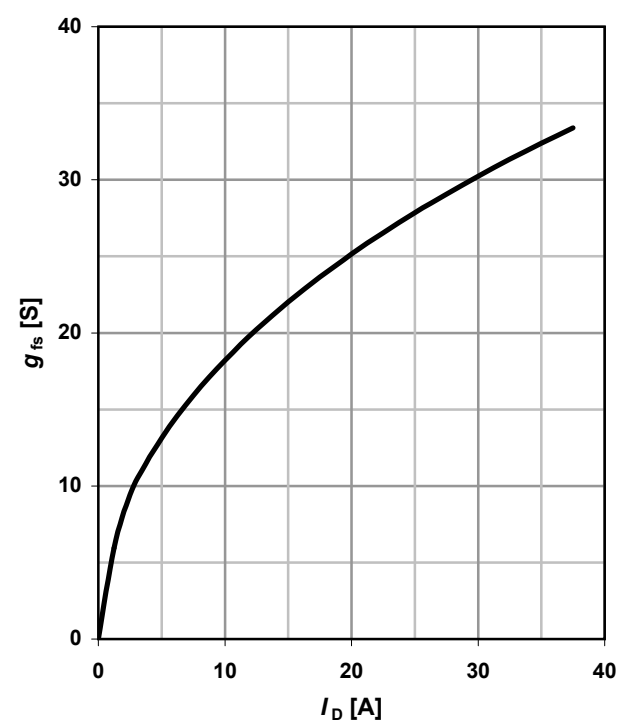
7 Typ. transfer characteristics

 $I_D = f(V_{GS}); V_{DS} = 6\text{V}$

parameter: T_j


8 Typ. Forward transconductance

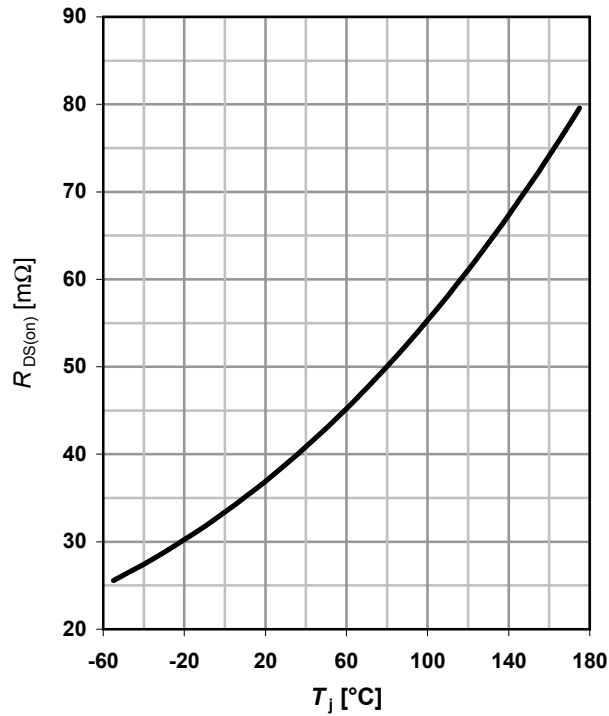
 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

parameter: g_{fs}


9 Typ. Drain-source on-state resistance

$$R_{DS(on)} = f(T_j)$$

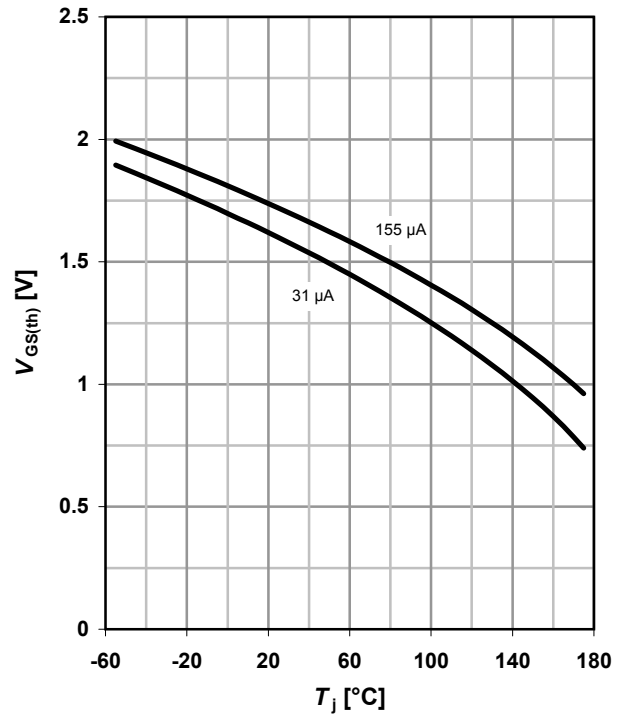
parameter: $I_D = 11\text{ A}$; $V_{GS} = 10\text{ V}$



10 Typ. gate threshold voltage

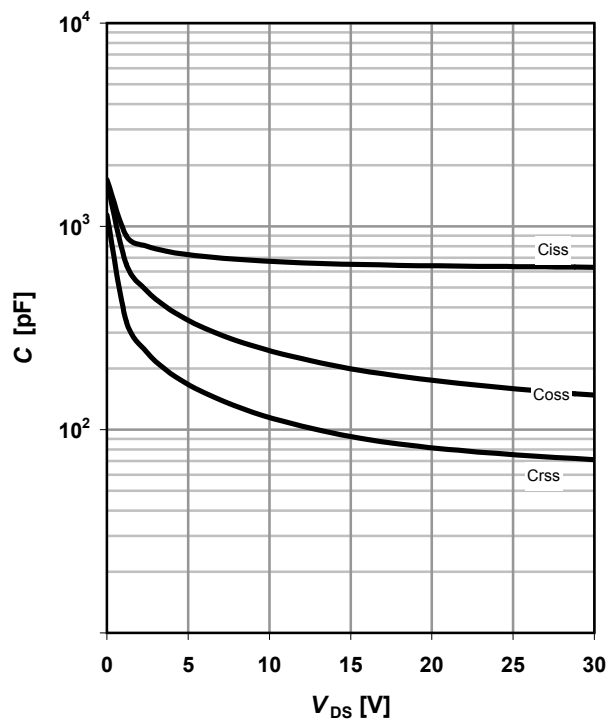
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}$$

parameter: I_D



11 Typ. capacitances

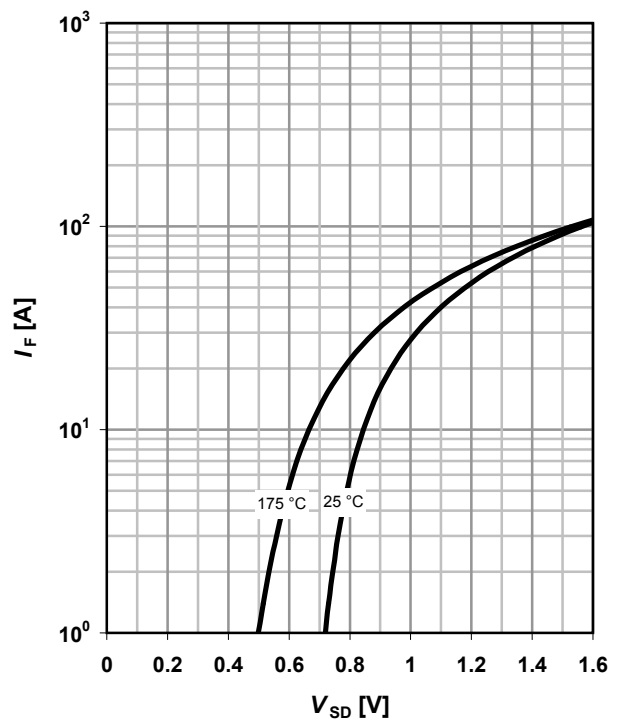
$$C = f(V_{DS}); V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$



12 Typical forward diode characteristics

$$I_F = f(V_{SD})$$

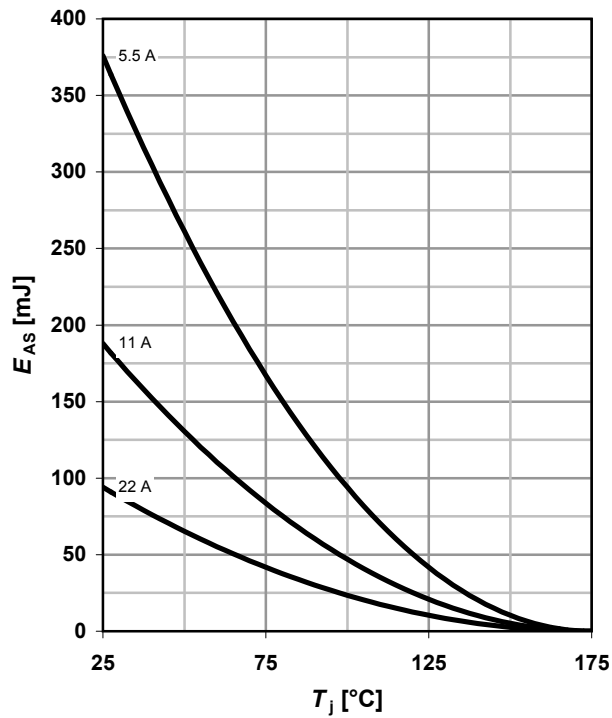
parameter: T_j



13 Typical avalanche energy

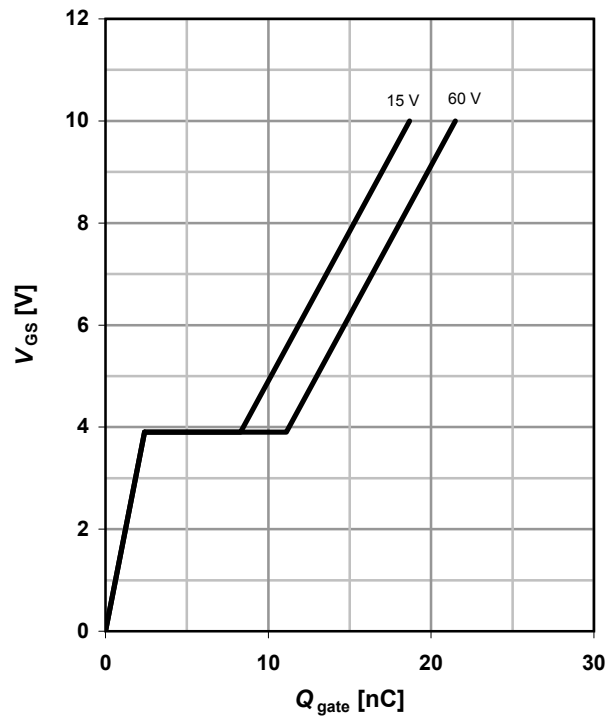
$$E_{AS} = f(T_j)$$

parameter: I_D



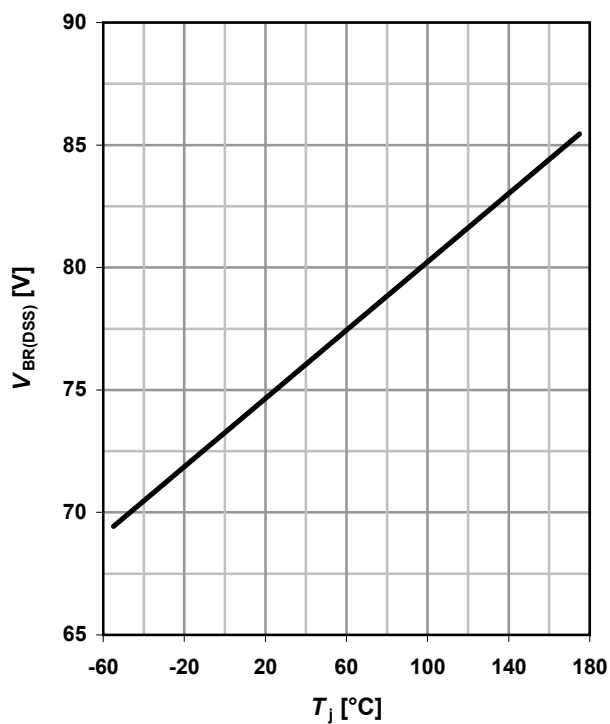
14 Typ. gate charge

$$V_{GS} = f(Q_{gate}); I_D = 22 \text{ A pulsed}$$

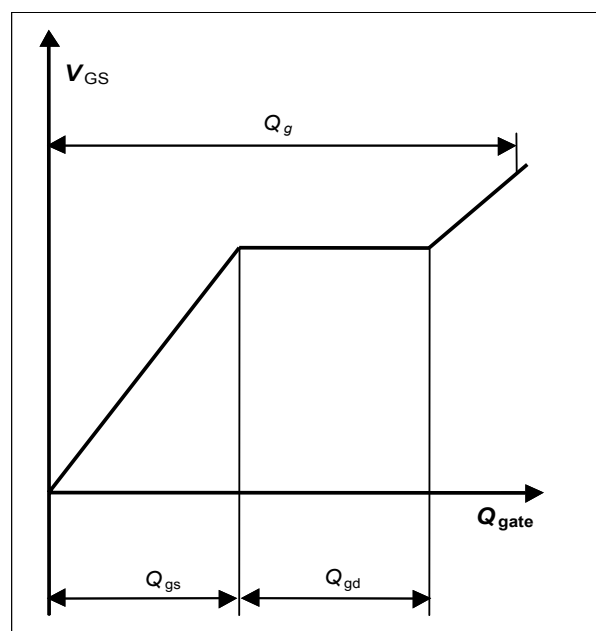


15 Typ. drain-source breakdown voltage

$$V_{BR(DSS)} = f(T_j); I_D = 1 \text{ mA}$$



16 Gate charge waveforms



Published by
Infineon Technologies AG
Am Campeon 1-12
D-85579 Neubiberg
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